



# HiPerFRED

$V_{RRM}$	=	300 V
$I_{FAV}$	=	30 A
$t_{rr}$	=	35 ns

High Performance Fast Recovery Diode  
Low Loss and Soft Recovery  
Single Diode

Part number

**DPG30IM300PC**

Marking on Product: *DPG30IM300PC*



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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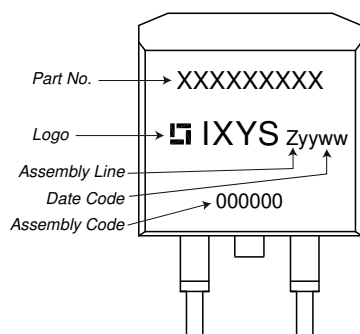
Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			300	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			300	V	
$I_R$	reverse current, drain current	$V_R = 300\text{ V}$	$T_{VJ} = 25^{\circ}C$		1	$\mu A$	
		$V_R = 300\text{ V}$	$T_{VJ} = 150^{\circ}C$		0.1	mA	
$V_F$	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}C$		1.35	V	
		$I_F = 60\text{ A}$			1.66	V	
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}C$			1.08	V
		$I_F = 60\text{ A}$				1.43	V
$I_{FAV}$	average forward current	$T_C = 140^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		30	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.70	V	
$r_F$	slope resistance				11.1	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.85	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		175	W	
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}C$		360	A	
$C_J$	junction capacitance	$V_R = 150\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		42	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 200\text{ V}$ $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}C$		3	A	
			$T_{VJ} = 125^{\circ}C$		7	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 25^{\circ}C$		35	ns	
			$T_{VJ} = 125^{\circ}C$		55	ns	



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$F_C$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

**Product Marking**



**Part description**

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 30 = Current Rating [A]
- IM = Single Diode
- 300 = Reverse Voltage [V]
- PC = TO-263AB (D2Pak) (2)

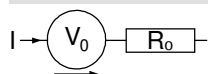
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30IM300PC-TRL	DPG30IM300PC	Tape & Reel	800	510002
Alternative	DPG30IM300PC-TUB	DPG30IM300PC	Tube	50	525113

Similar Part	Package	Voltage class
DSEP40-03AS	TO-263AB (D2Pak) (2)	300
DPG60IM300PC	TO-263AB (D2Pak) (2)	300

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 175\text{°C}$



**Fast Diode**

$V_{0\ max}$	threshold voltage	0.7	V
$R_{0\ max}$	slope resistance *	7.8	mΩ



**Outlines TO-263 (D2Pak)**



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2.54 BSC		0.100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

*All dimensions conform with and/or within JEDEC standard.*





**Fast Diode**

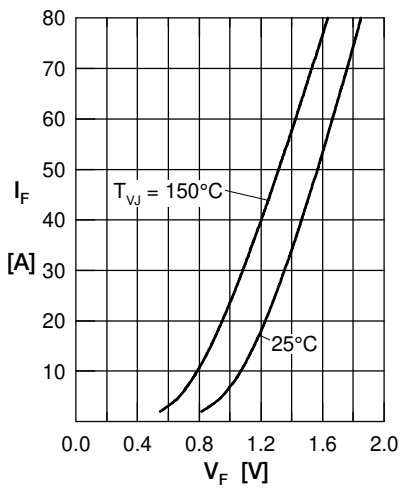


Fig. 1 Forward current  $I_F$  versus  $V_F$

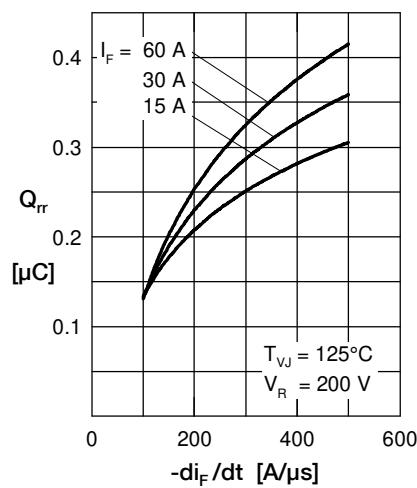


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$

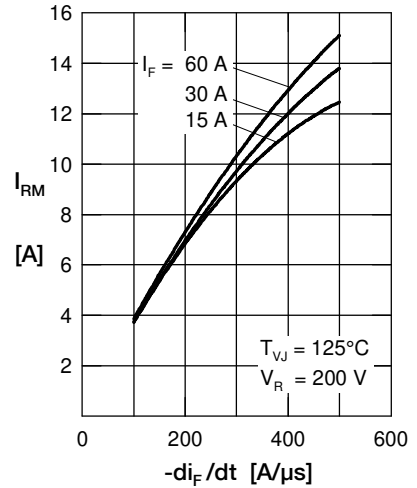


Fig. 3 Typ. reverse recov. current  $I_{RM}$  versus  $-di_F/dt$

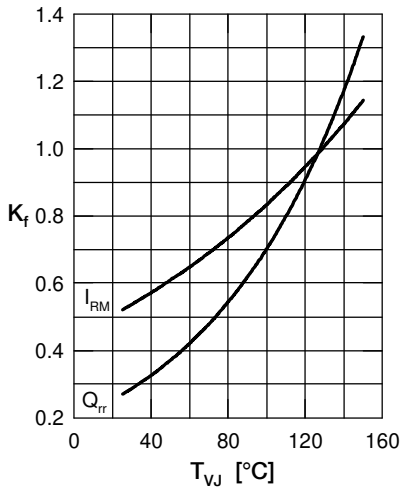


Fig. 4 Typ. dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

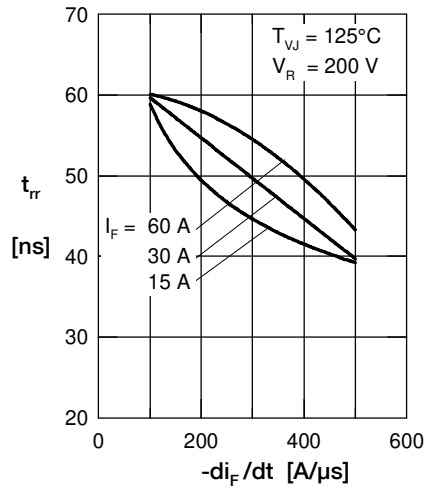


Fig. 5 Typ. reverse recov. time  $t_{rr}$  versus  $-di_F/dt$

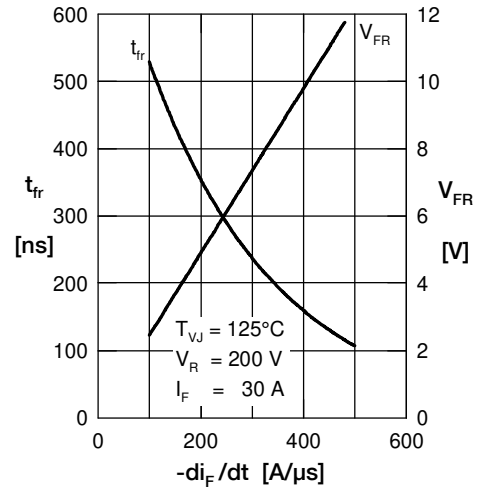


Fig. 6 Typ. forward recov. voltage  $V_{FR}$  &  $t_{fr}$  versus  $di_F/dt$

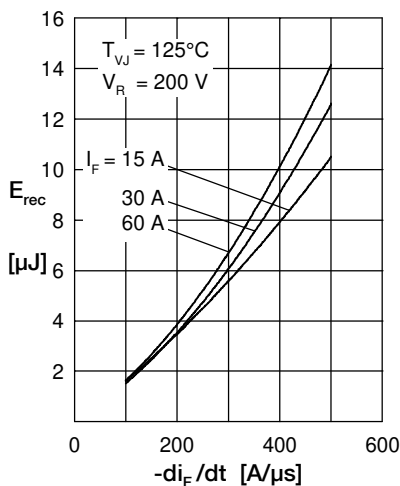


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

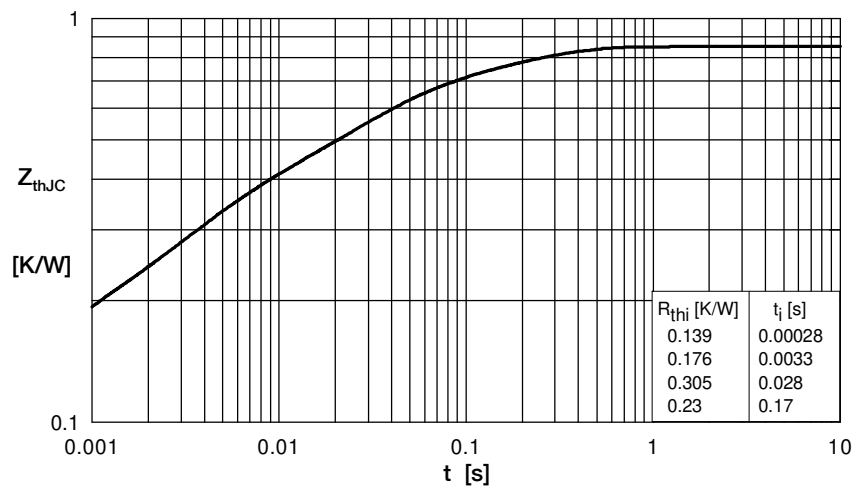


Fig. 8 Transient thermal impedance junction to case